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November 2013

## **FQP85N06**

# N-Channel QFET<sup>®</sup> MOSFET 60 V, 85 A, 10 m $\Omega$

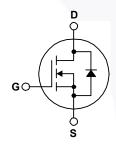
#### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### **Features**

- 85 A, 60 V,  $R_{DS(on)}$  = 10 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 42.5 A
- Low Gate Charge (Typ. 86 nC)
- Low Crss (Typ. 165 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP85N06	Unit
V <sub>DSS</sub>	Drain-Source Voltage		60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	(Note 5)	85	Α
	- Continuous (T <sub>C</sub> = 100°C	)	60	Α
DM	Drain Current - Pulsed	(Note 1)	300	Α
/ <sub>GSS</sub>	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	810	mJ
l <sub>AR</sub>	Avalanche Current	(Note 1)	85	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	16.0	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		160	W
	- Derate above 25°C		1.07	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQP85N06	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.94	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP85N06	FQP85N06	TO-220	Tube	N/A	N/A	50 units

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T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.06		V/°C
I <sub>DSS</sub>	Zero Osto Veltoro Broin Ormant	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10 V, I <sub>D</sub> =42.5 A		0.008	0.010	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 42.5 A	\	54		S
	ic Characteristics			3170	4120	nE.
Ciss	Input Capacitance Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$		1150	1500	pF pF
C <sub>oss</sub> C <sub>rss</sub>	Reverse Transfer Capacitance			165	220	рF
Orss	Reverse Transfer Capacitatice			103	220	рі
Switch	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 42.5 \text{ A},$ $R_{G} = 25 \Omega$		40	90	ns
t <sub>r</sub>	Turn-On Rise Time			230	470	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	3		175	360	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	170	350	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 85 A,	-	86	112	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		20.5		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		36		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I <sub>S</sub>		Maximum Continuous Drain-Source Diode Forward Current (Note 5)			85	Α
-						
$I_{SM}$	Maximum Pulsed Drain-Source Diode F	orward Current			300	Α

## $Q_{rr}$

 $t_{rr}$ 

Reverse Recovery Time

Reverse Recovery Charge

- Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature. 2. L = 130  $\mu$ H, I<sub>AS</sub> = 85 A, V<sub>DD</sub> = 25 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  85 A, di/dt  $\leq$  300 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially Independent of Operating Temperature. 5. Continuous Drain Current Calculated by Maximum Junction Temperature: Limited by Package.

--

70

135

ns

nC

 $V_{GS} = 0 \text{ V, } I_{S} = 85 \text{ A,}$ 

 $dI_F / dt = 100 A/\mu s$ 

## **Typical Characteristics**

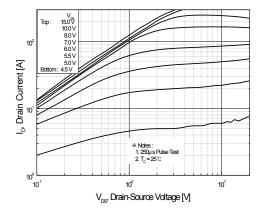


Figure 1. On-Region Characteristics

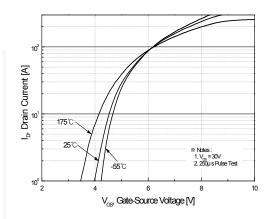


Figure 2. Transfer Characteristics

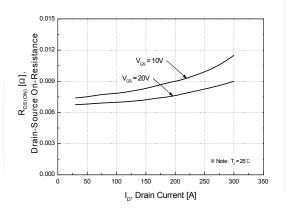


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

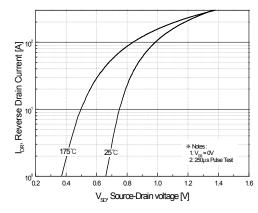


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

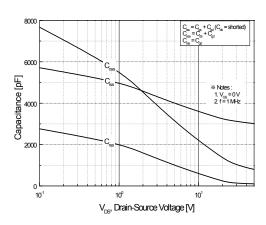


Figure 5. Capacitance Characteristics

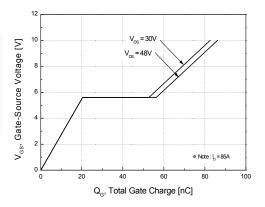


Figure 6. Gate Charge Characteristics

## **Typical Characteristics** (continued)

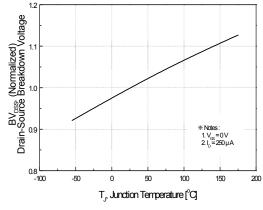


Figure 7. Breakdown Voltage Variation vs. Temperature

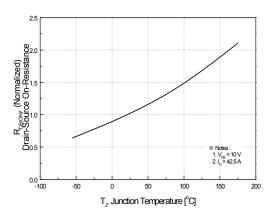


Figure 8. On-Resistance Variation vs. Temperature

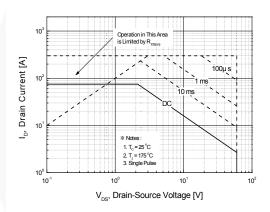


Figure 9. Maximum Safe Operating Area

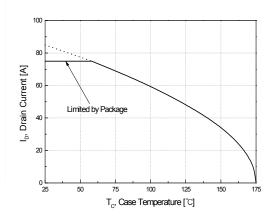


Figure 10. Maximum Drain Current vs. Case Temperature

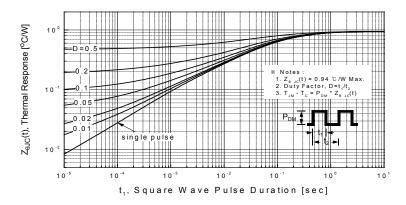


Figure 11. Transient Thermal Response Curve

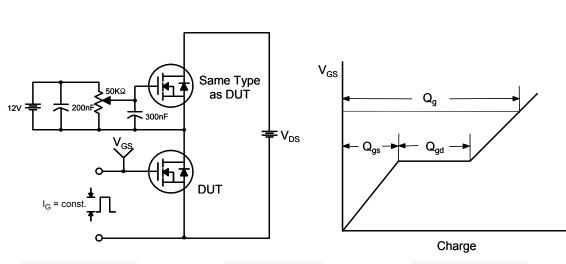


Figure 12. Gate Charge Test Circuit & Waveform

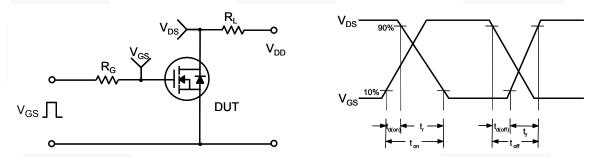


Figure 13. Resistive Switching Test Circuit & Waveforms

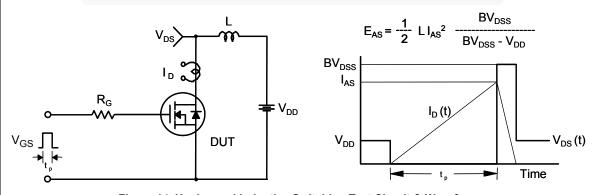
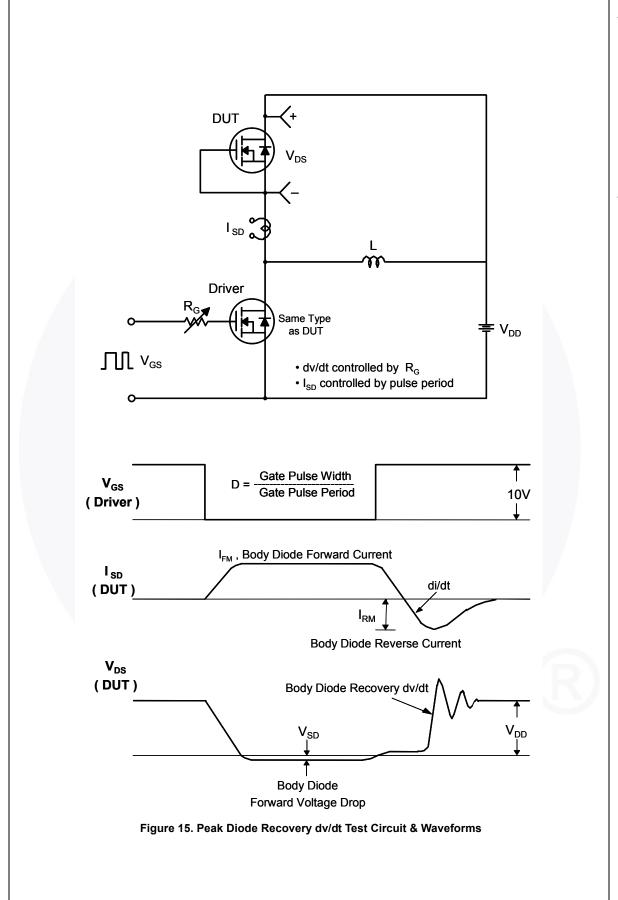


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**

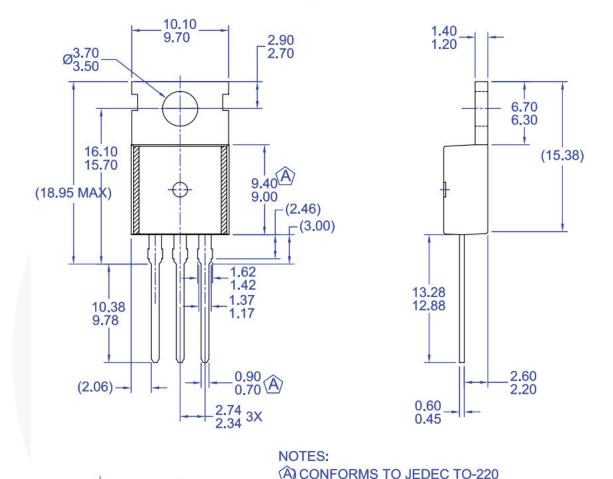


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

VARIATION AB EXCEPT WHERE NOTED

C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

B) ALL DIMENSIONS ARE IN MILLIMETERS.

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10.20

9.80

4.70

4.30





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